

SANYO Semiconductors DATA SHEET

2SA1433-

PNP Epitaxial Planar Silicon Transistor

High-Definition CRT Display Applications

Features

- · High fT (Gain-Bandwidth Product).
- Small reverse transfer capacitance (Cre=1.3pF).
- · Adoption of FBET process.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-70	V
Collector-to-Emitter Voltage	VCEO		-60	V
Emitter-to-Base Voltage	VEBO		-4	V
Collector Current	IC		-50	mA
Collector Current (Pulse)	ICP		-100	mA
Collector Dissipation	PC		900	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
		Conditions	min	typ	max	Onit
Collector Cutoff Current	ICBO	V _{CB} =-40V, I _E =0A			-0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =-3V, I _C =0A			-1.0	μΑ
DC Current Gain	hFE	VCE=-10V, IC=-10mA	60*		320*	
Gain-Bandwidth Product	fΤ	V _{CE} =-10V, I _C =-10mA	350	700		MHz
Base-to-Collector Time Contact	r _{bb} ´Cc	V _{CE} =-10V, I _C =-10mA		8		pF
Output Capacitance	Cob	VCB=-10V, f=1MHz		1.7		рF
Reverse Transfer Capacitance	Cre	V _{CB} =-10V, f=1MHz		1.3		рF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =-20mA, I _B =-2mA			-0.6	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=-20mA, IB=-2mA			-1.0	٧
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =-10μA, I _E =0A	-70			٧
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, RBE=∞	-60			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =-10μA, I _C =0A	-4			V

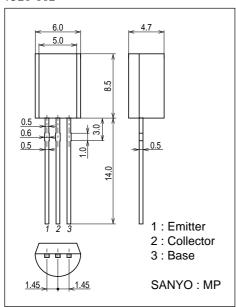
*: The 2SA1433 is classified by 10mA hFE as follows:

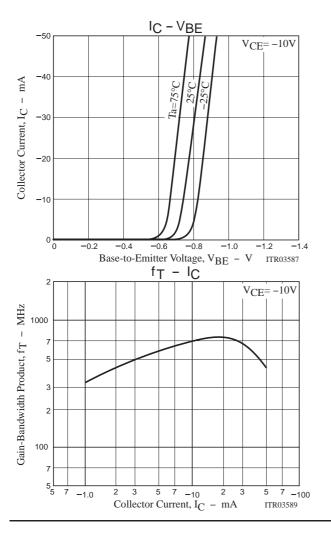
Rank	D	Е	F	
hFE	60 to 120	100 to 200	160 to 320	

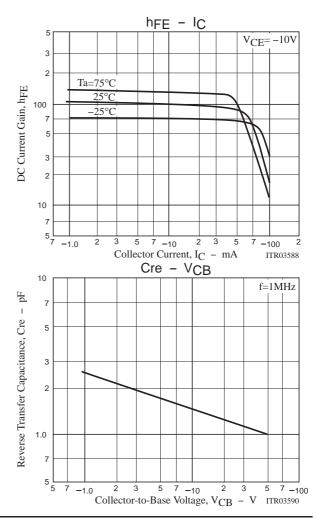
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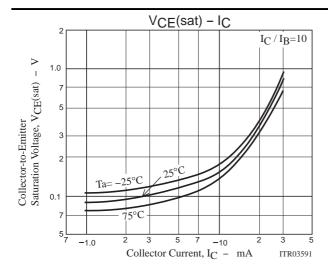
Package Dimensions

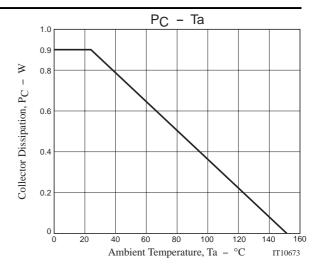
unit : mm 7520-002











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